

SANYO Semiconductors DATA SHEET

CPH6532 — NPN Epitaxial Planar Silicon Transistor

DC / DC Converter Applications

Applications

· Relay drivers, lamp drivers, motor drivers, flash.

Features

- · Composite type with two NPN transistors contained in one package facilitating high-density mounting.
- The two chips contained are equivalent to the CPH3216.
- Ultrasmall package permitting applied sets to be small and slim.

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	VCBO		80	V
Collector-to-Emitter Voltage	VCES		80	V
Collector-to-Emitter Voltage	VCEO		50	V
Emitter-to-Base Voltage	VEBO		5	V
Collector Current	IC		1.0	Α
Collector Current (Pulse)	lCP		2	Α
Base Current	lΒ		200	mA
Collector Dissipation	PC	Mounted on a ceramic board (600mm²X0.8m) 1unit	0.9	W
Total Power Dissipation	PT	Mounted on a ceramic board (600mm²×0.8m)	1.1	W
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Offic
Collector Cutoff Current	ICBO	V _{CB} =40V, I _E =0A			0.1	μΑ
Emitter Cutoff Current	IEBO	V _{EB} =4V, I _C =0A			0.1	μΑ
DC Current Gain	hFE	V _{CE} =2V, I _C =100mA	200		560	
Gain-Bandwidth Product	fŢ	VCE=10V, IC=300mA		420		MHz
Output Capacitance	Cob	V _{CB} =10V, f=1MHz		6		pF

Marking: ET Continued on next page.

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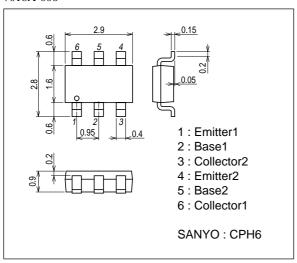
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Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Offic
Collector-to-Emitter Saturation Voltage	VCE(sat)1	IC=500mA, IB=10mA		130	190	mV
	V _{CE} (sat)2	I _C =300mA, I _B =6mA		90	135	mV
Base-to-Emitter Saturation Voltage	VBE(sat)	IC=500mA, IB=10mA		0.81	1.2	V
Collector-to-Base Breakdown Voltage	V(BR)CBO	IC=10μA, IE=0A	80			V
Collector-to-Emitter Breakdown Voltage	V(BR)CES	I _C =100μA, R _{BE} =0Ω	80			٧
Collector-to-Emitter Breakdown Voltage	V(BR)CEO	IC=1mA, RBE=∞	50			V
Emitter-to-Base Breakdown Voltage	V(BR)EBO	I _E =10μA, I _C =0A	5			V
Turm-ON Time	ton	See specified Test Circuit.		38		ns
Storage Time	tstg	See specified Test Circuit.		332		ns
Fall Time	tf	See specified Test Circuit.		40		ns

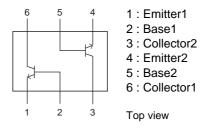
Note) The specifications shown above are for each individual transistor.

Package Dimensions

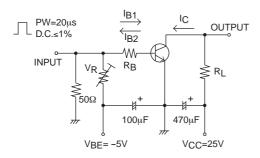
unit : mm (typ) 7018A-006



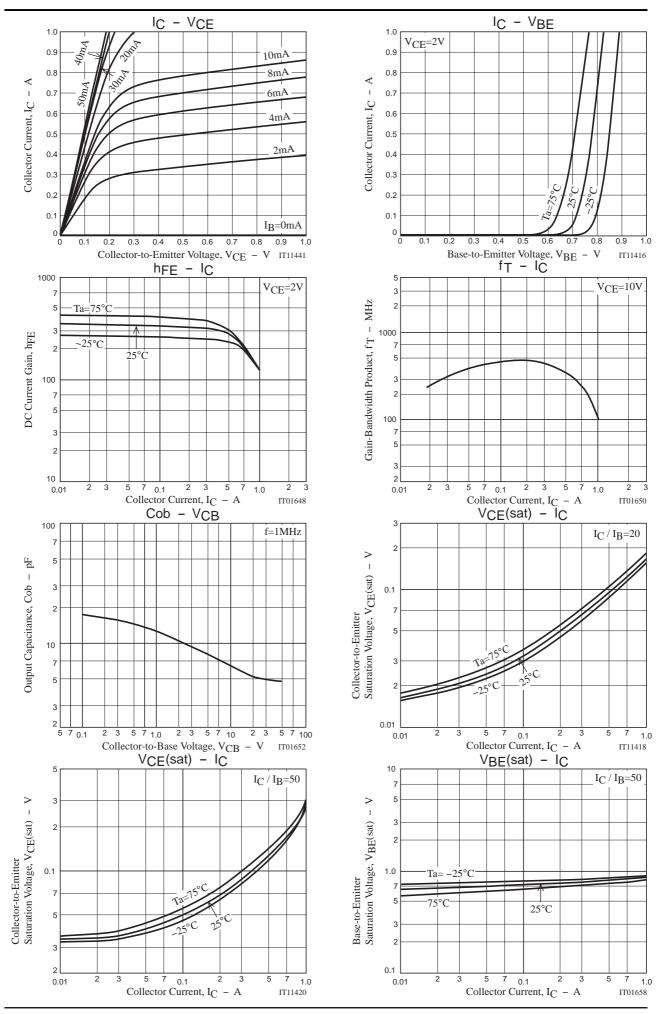
Electrical Connection



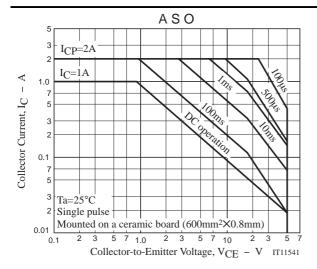
Switching Time Test Circuit

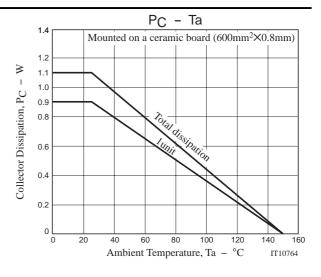


 $20I_{B1} = -20I_{B2} = I_{C} = 500mA$



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